

# Radar Pulsed Power Transistor 55W, 1.2-1.4 GHz, 1ms Pulse, 10% Duty

M/A-COM Products Released, 30 May 07

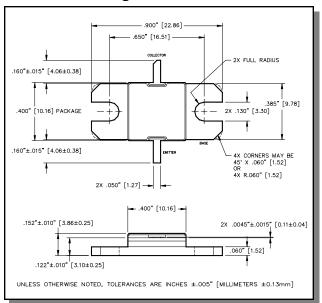
#### **Features**

- NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- · RoHS compliant

## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	$V_{CES}$	58	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	I <sub>C</sub>	7.0	Α
Power Dissipation @ +25°C	P <sub>TOT</sub>	220	W
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

### **Outline Drawing**



## Electrical Specifications: T<sub>C</sub> = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 120mA		BV <sub>CES</sub>	58	-	V
Collector-Emitter Leakage Current	V <sub>CE</sub> = 28V		I <sub>CES</sub>	-	6.0	mA
Thermal Resistance	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	R <sub>TH(JC)</sub>	-	0.8	°C/W
Output Power	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	P <sub>OUT</sub>	55	-	W
Power Gain	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	G <sub>P</sub>	6.6	-	dB
Collector Efficiency	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	ης	50	i	%
Input Return Loss	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	RL	-	-10	dB
Load Mismatch Tolerance	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 28V, Pin = 12W	F = 1.2, 1.3, 1.4 GHz	VSWR-S	-	1.5:1	-

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

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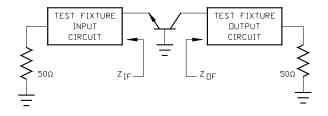


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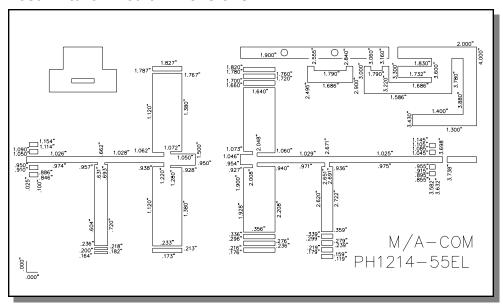
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## **RF Test Fixture Impedance**

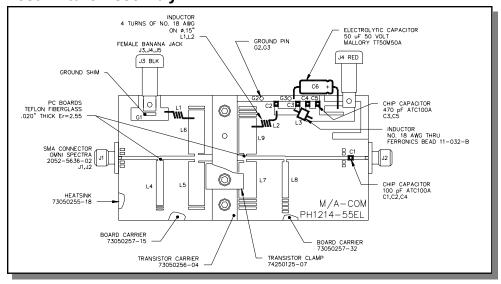
F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)
1.2	5.8 + j1.8	5.5 - j3.4
1.3	2.4 + j1.3	3.3 - j2.3
1.4	2.4 + j0.6	2.0 - j2.3



#### **Test Fixture Circuit Dimensions**



#### **Test Fixture Assembly**



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